

Description

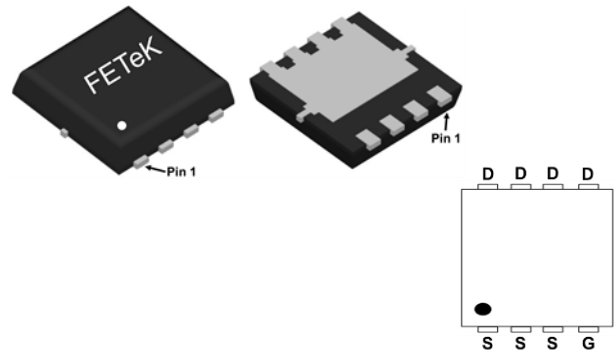
- Advanced Trench MOS Technology
- Low Gate Charge
- Low $R_{DS(ON)}$
- 100% EAS Guaranteed
- Green Device Available

Application

- Motor Control.
- DC/DC Converter.
- Synchronous rectifier applications.

Product Summary


BVDSS	RDSON	ID
60V	8.5mΩ	30A

PRPAK3x3 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current ^{1,6}	30	A
$I_D@T_C=100^\circ C$		27	A
I_{DM}	Pulsed Drain Current ²	100	A
EAS	Single Pulse Avalanche Energy ³	26.5	mJ
I_{AS}	Avalanche Current	23	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	27.7	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹ ($t \leq 10S$)	---	25	°C/W
	Thermal Resistance Junction-ambient ¹ (Steady State)	---	55	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case ¹	---	4.5	°C/W

**Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=15A$	---	7.0	8.5	m Ω
		$V_{GS}=4.5V, I_D=15A$	---	10.5	12.5	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=48V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=48V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.3	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=30V, V_{GS}=10V, I_D=15A$	---	15	---	nC
Q_{gs}	Gate-Source Charge		---	3.5	---	
Q_{gd}	Gate-Drain Charge		---	4.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V, V_{GS}=10V, R_G=3.3\Omega, I_D=15A$	---	7	---	ns
T_r	Rise Time		---	4.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	26	---	
T_f	Fall Time		---	5	---	
C_{iss}	Input Capacitance	$V_{DS}=30V, V_{GS}=0V, f=1\text{MHz}$	---	1270	---	pF
C_{oss}	Output Capacitance		---	479	---	
C_{riss}	Reverse Transfer Capacitance		---	40	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5,6}	$V_G=V_D=0V$, Force Current	---	---	30	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=15A, dI/dt=100A/\mu s,$	---	22	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	72	---	nC

Note :

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- Single pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$.
- The EAS data shows Max. rating . The test condition is $V_{DD}=50V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=23A$
- The power dissipation is limited by 150°C junction temperature
- The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.
- The maximum current rating is package limited.

Typical Characteristics

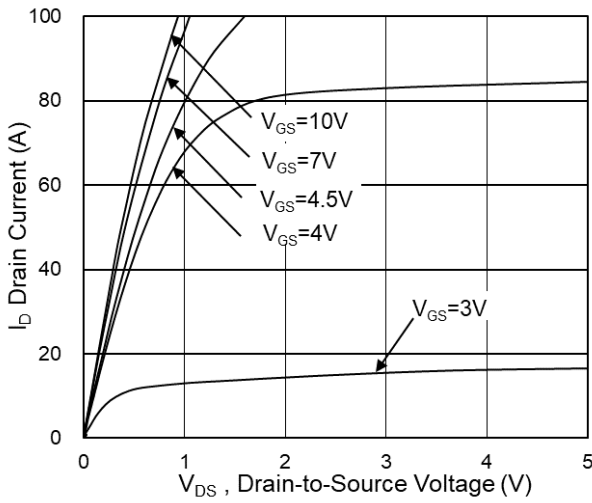


Fig.1 Typical Output Characteristics

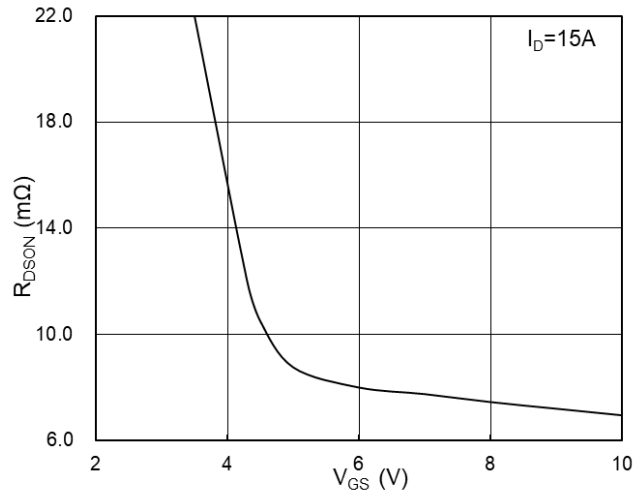


Fig.2 On-Resistance vs G-S Voltage

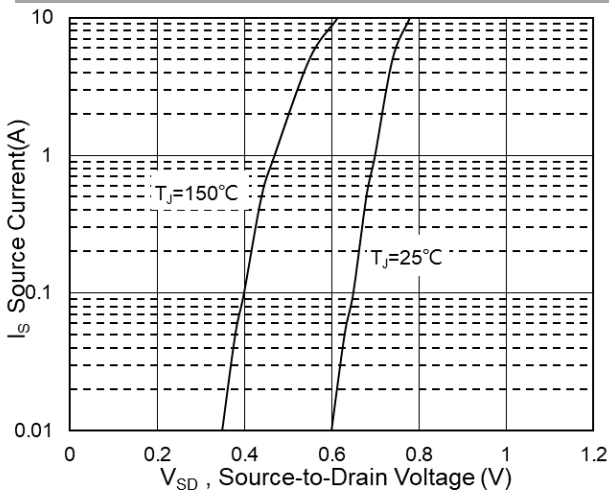


Fig.3 Source Drain Forward Characteristics

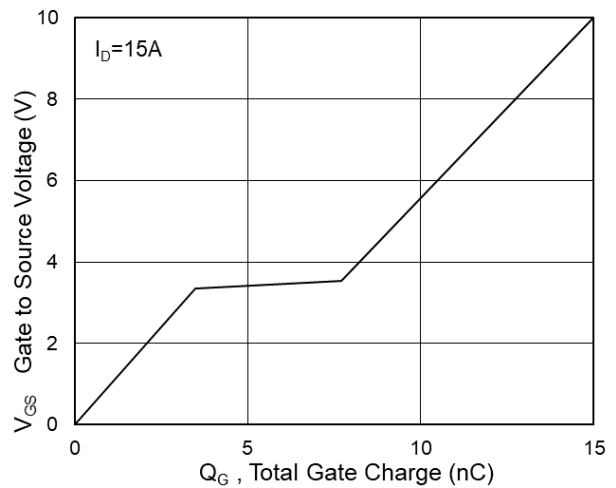


Fig.4 Gate-Charge Characteristics

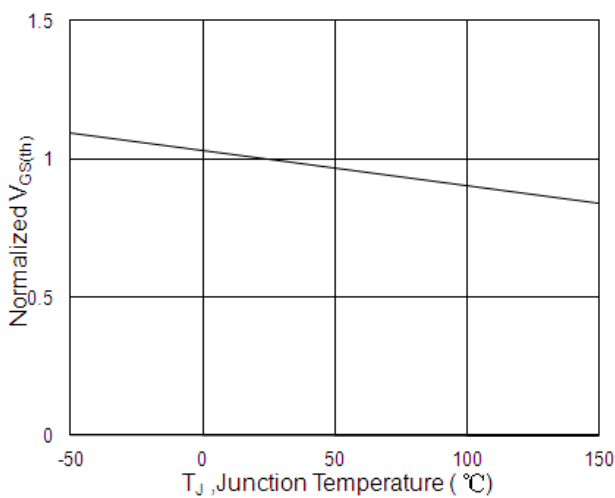


Fig.5 Normalized $V_{GS(th)}$ vs T_J

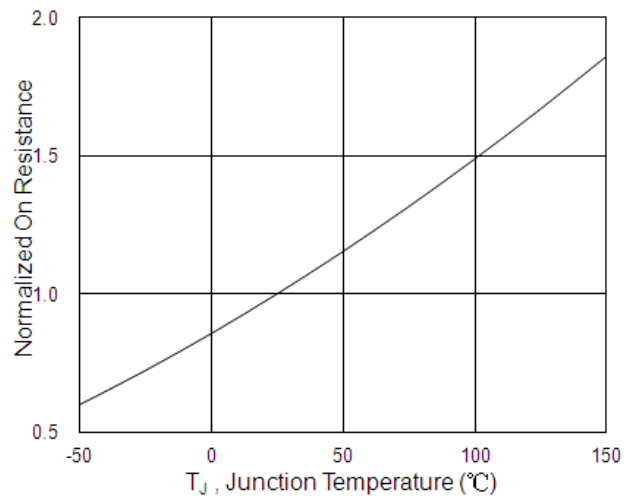


Fig.6 Normalized R_{DSON} vs T_J

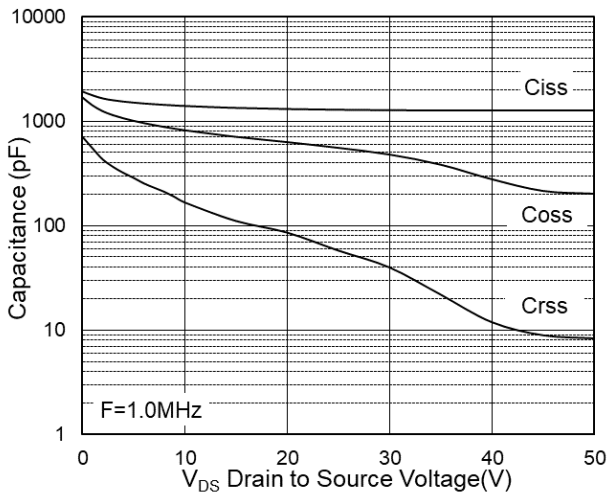


Fig.7 Capacitance

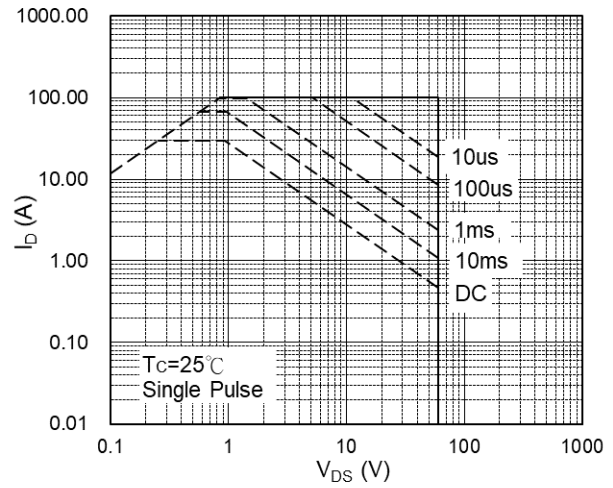


Fig.8 Safe Operating Area

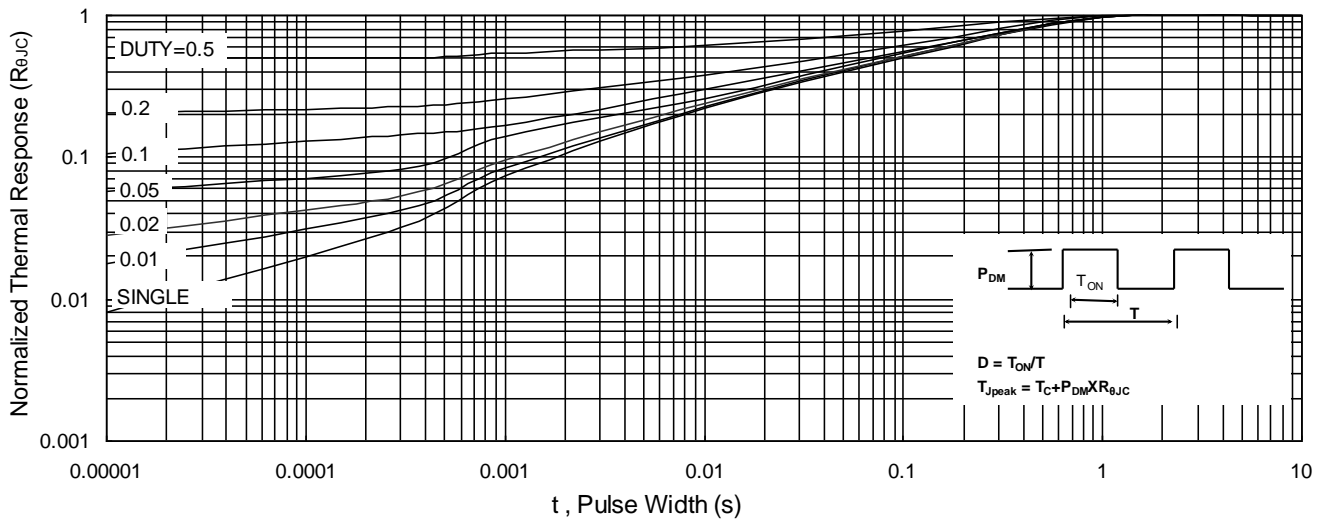


Fig.9 Normalized Maximum Transient Thermal Impedance

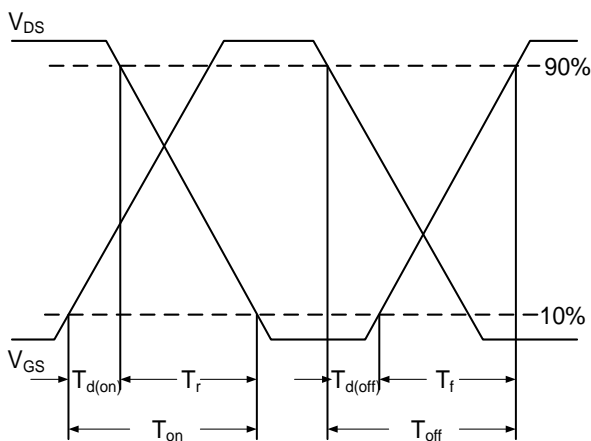


Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

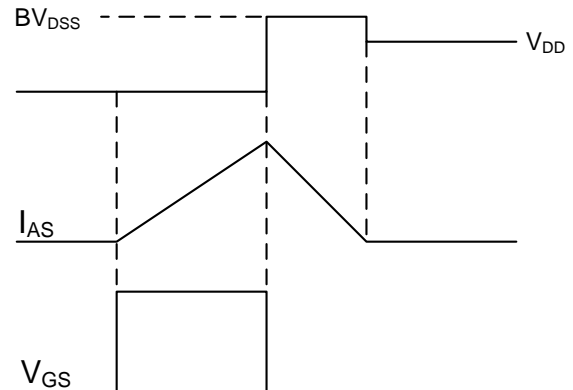


Fig.11 Unclamped Inductive Switching Waveform